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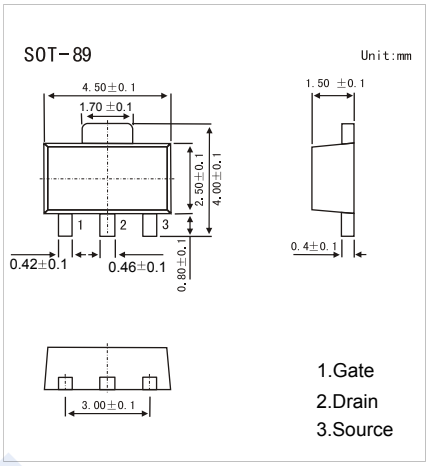
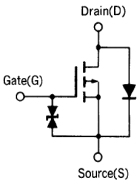


■ Features

- $V_{DS\ (V)}$ =-100V
- I_D =-1 A (V_{GS} =-10V)
- $R_{DS(ON)}$ < 2Ω (V_{GS} =-10V)
- $R_{DS(ON)}$ < 2.5Ω (V_{GS} =-4V)



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	±20	
Continuous Drain Current	I_D	-1	A
Pulsed Drain Current (Note.1)	I_{DM}	-2	
Power Dissipation Tc = 25℃	P_D	2	W
Junction Temperature	T_J	150	℃
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: PW ≤ 10 ms, duty cycle ≤ 50%

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=-250μA, V_{GS}=0V	-100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-100V, V_{GS}=0V			-10	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±10	uA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	V_{GS}=-10V I_D=-1mA	-1		-3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-0.5A			2	Ω
		V_{GS}=-4V, I_D=-0.5A			2.5	
Forward Transconductance	g_{FS}	V_{DS}=-10V, I_D=-0.5A	0.4	0.9		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-10V, f=1MHz		220		pF
Output Capacitance	C_{oss}			85		
Reverse Transfer Capacitance	C_{rss}			8		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)}$=-10V, I_D=-0.5A, R_L=50Ω, R_G=10Ω, V_{DD}=-25V,		45		ns
Turn-On Rise Time	t_r			36		
Turn-Off DelayTime	$t_{d(off)}$			360		
Turn-Off Fall Time	t_f			90		

■ Marking

Marking	PC

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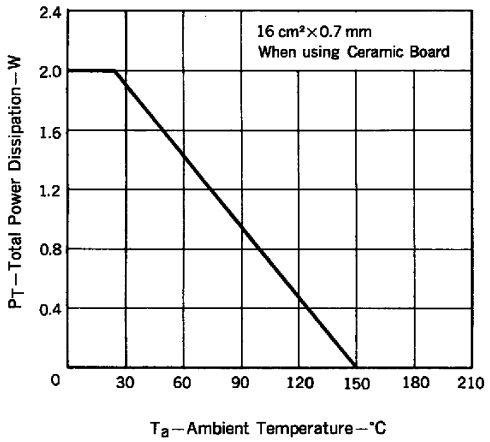
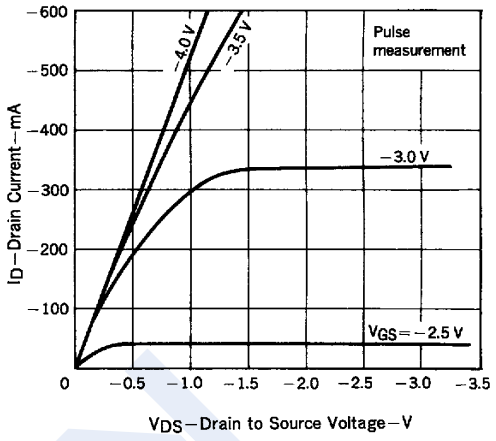
■ Typical Characterisitics

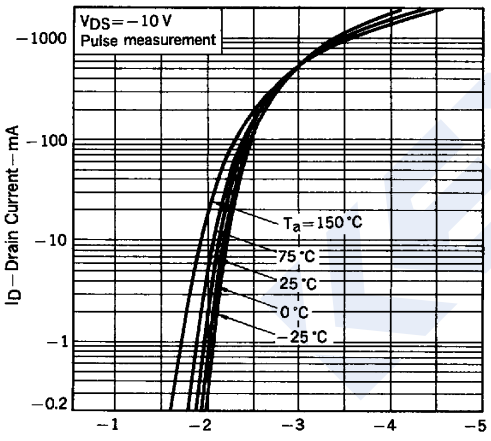
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



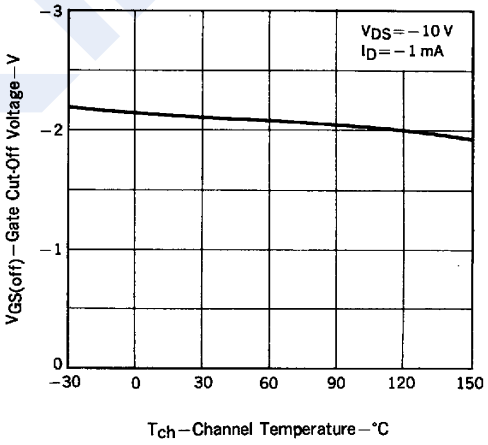
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



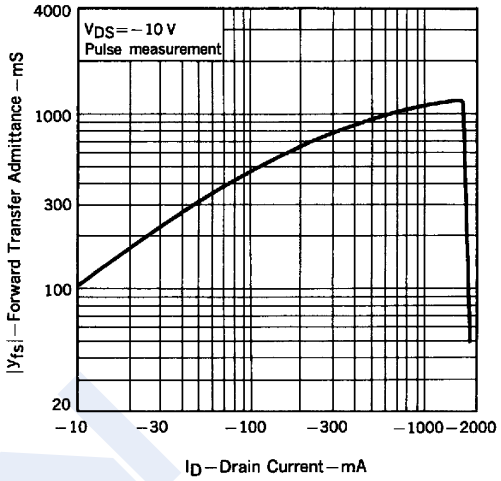
TRANSFER CHARACTERISTICS



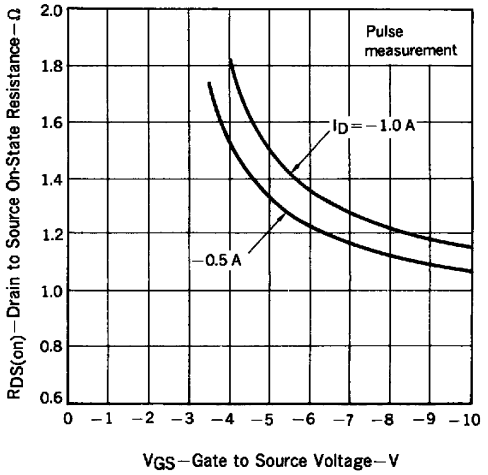
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



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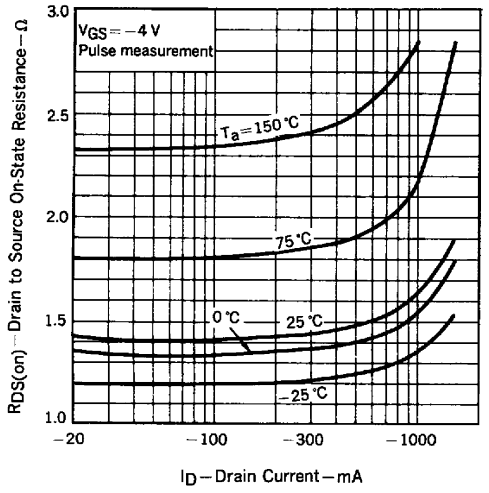
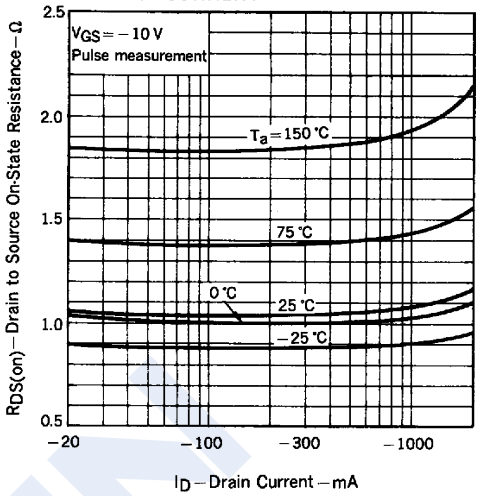
■ Typical Characterisitics

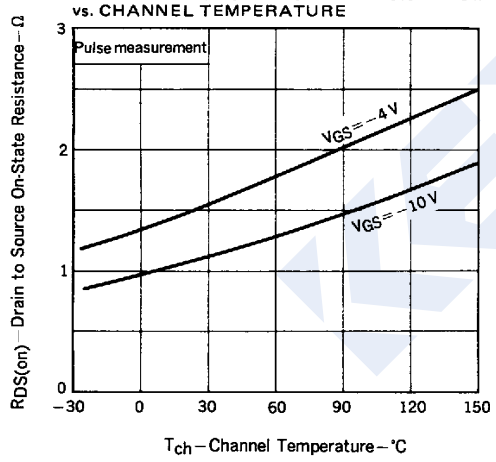
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



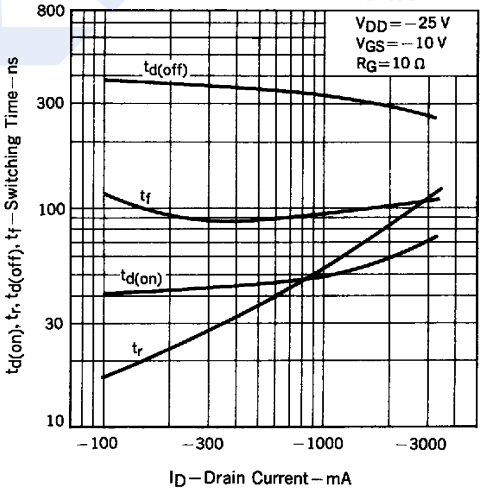
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



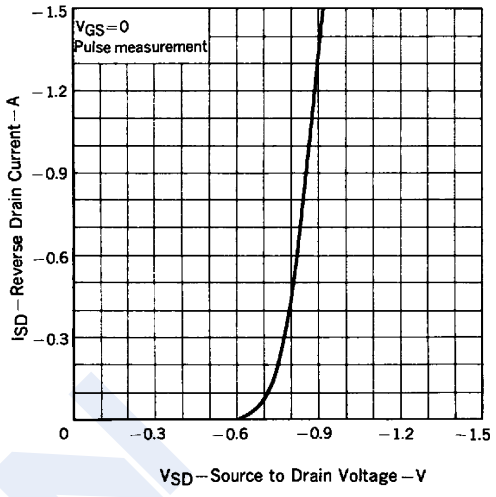
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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■ Typical Characterisitics